

GSM8989

60V P-Channel Enhancement Mode MOSFET

Product Description

GSM8989, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

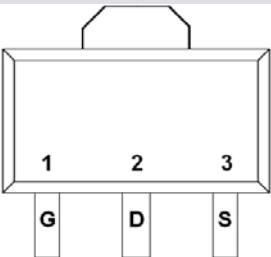
Features

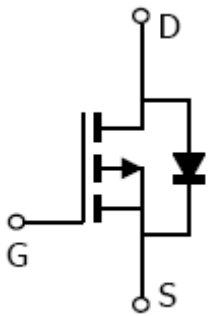
- -60V/-3.6A, $R_{DS(ON)}=115m\Omega@V_{GS}=-10V$
- -60V/-2.6A, $R_{DS(ON)}=125m\Omega@V_{GS}=-4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- SOT-89-3L package design

Applications

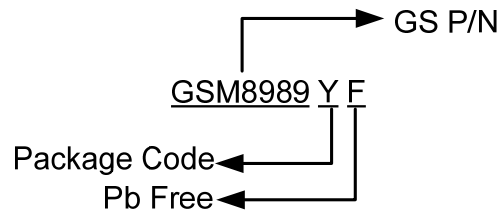
- Motor and Load Control
- LCD TV Inverter & AD/DC Inverter Systems.
- Backlight Inverter for LCD Display
- Load Switch
- CCFL Inverter

Packages & Pin Assignments

GSM8989YF(SOT-89-3L)	
	
Pin	Description
1	Gate
2	Drain
3	Source

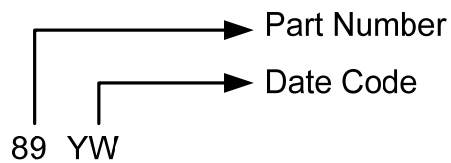


Ordering Information



Part Number	Package	Quantity Reel
GSM8989YF	SOT-89-3L	1000 PCS

Marking Information



Absolute Maximum Ratings

T_A=25°C Unless otherwise noted

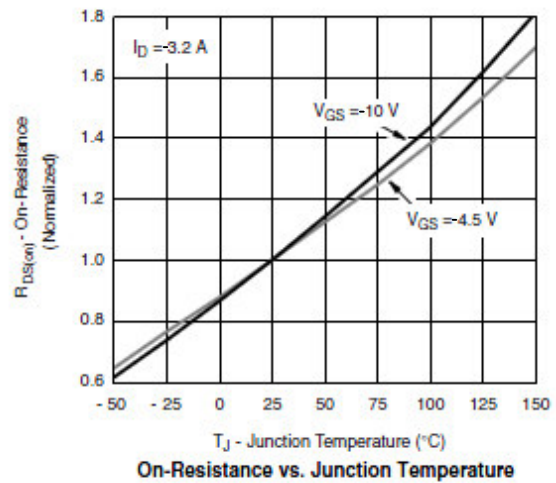
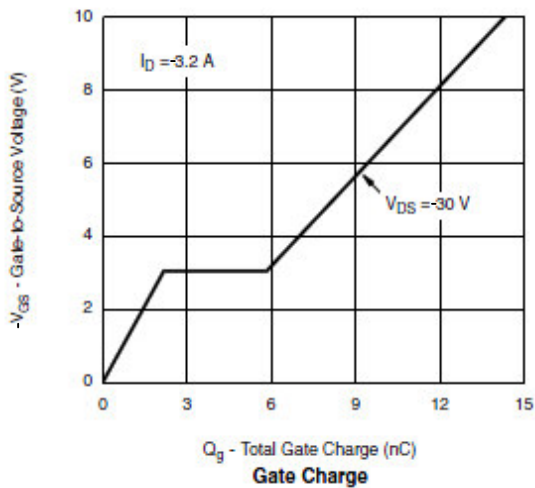
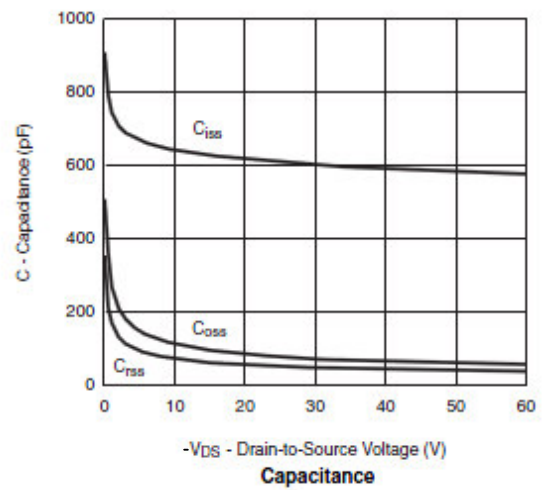
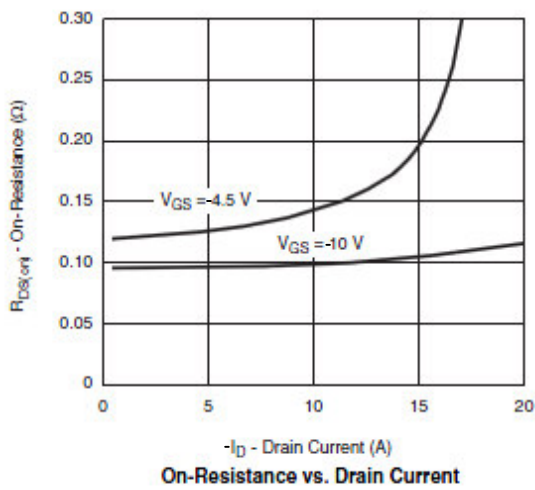
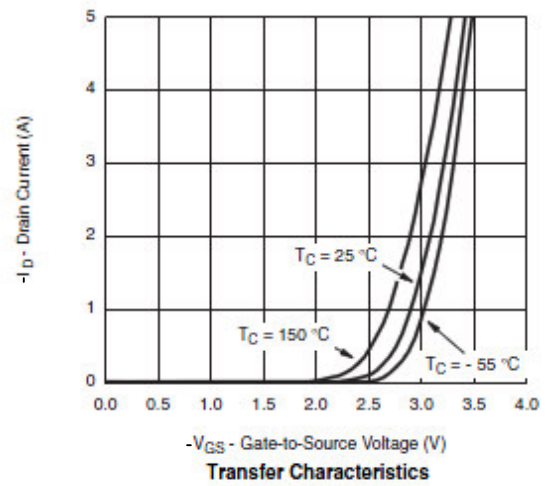
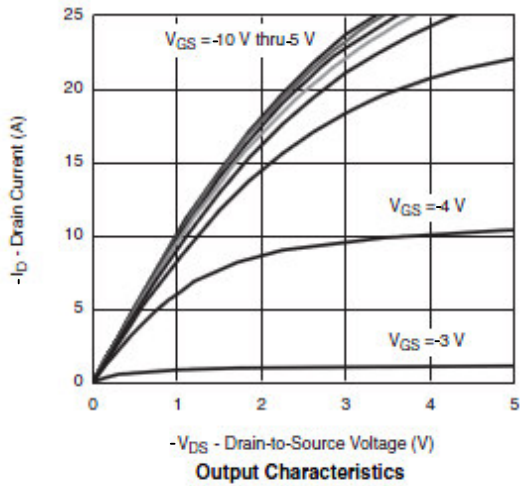
Symbol	Parameter	Typical	Unit	
V _{DSS}	Drain-Source Voltage	-60	V	
V _{GSS}	Gate -Source Voltage	±20	V	
I _D	Continuous Drain Current(T _J =150°C)	T _A =25°C	-3.6	A
		T _A =70°C	-2.6	
I _{DM}	Pulsed Drain Current	-10	A	
I _S	Continuous Source Current(Diode Conduction)	-1.6	A	
P _D	Power Dissipation	T _A =25°C	1.45	W
		T _A =70°C	0.6	
T _J	Operating Junction Temperature	150	°C	
T _{STG}	Storage Temperature Range	-55/150	°C	
R _{θJA}	Thermal Resistance-Junction to Ambient	120	°C/W	

Electrical Characteristics

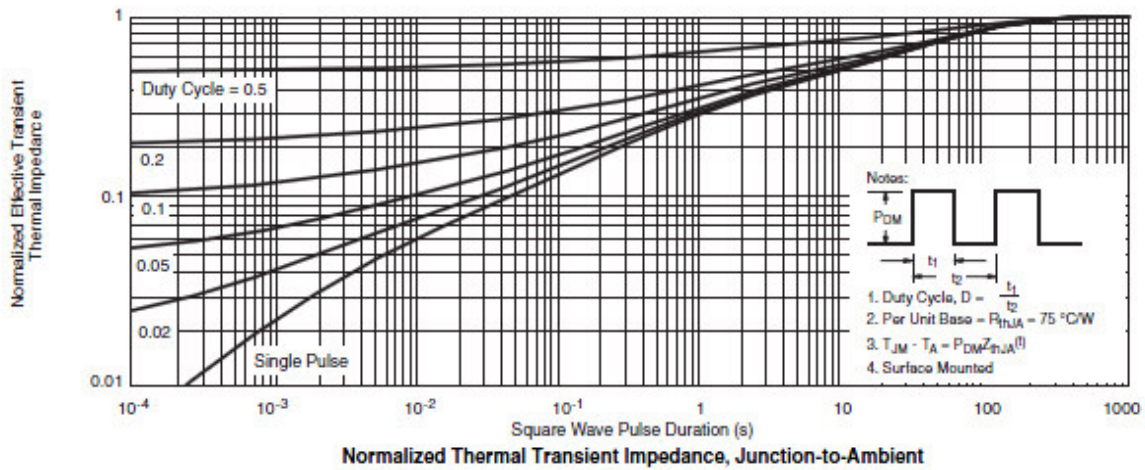
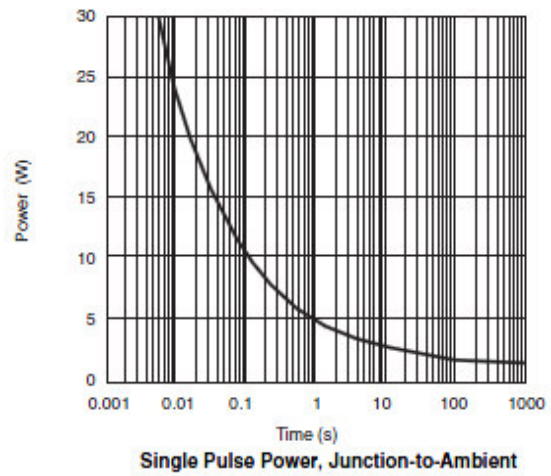
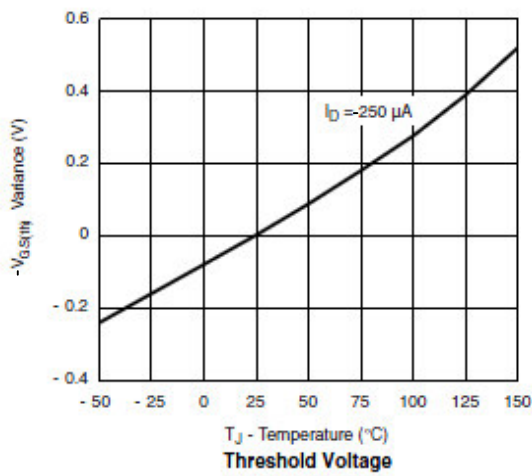
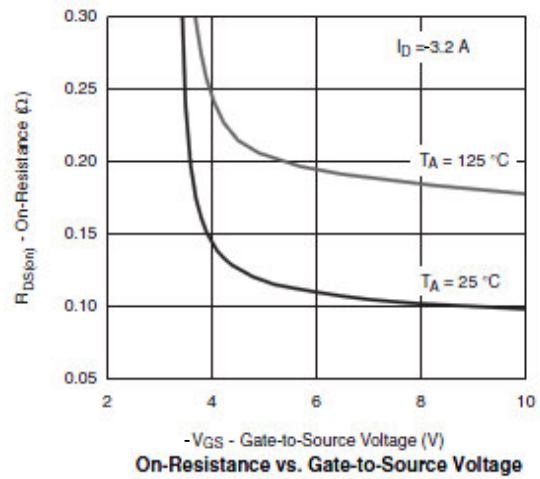
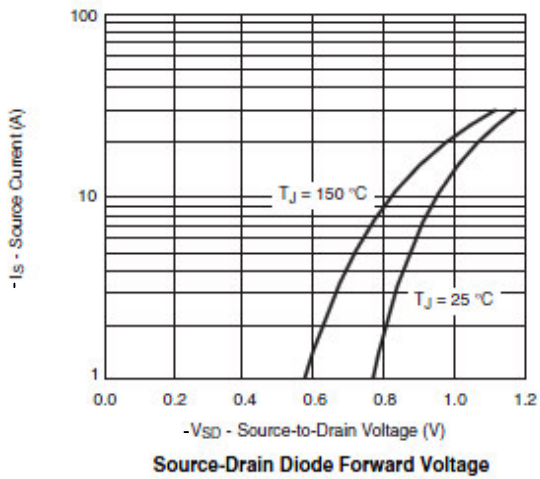
T_A=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250uA	-60			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250uA	-0.8		-2.5	
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} = ±20V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -48V, V _{GS} =0V			-1	uA
		V _{DS} =-48V, V _{GS} =0V, T _J =85°C			-20	
I _{D(on)}	On-State Drain Current	V _{DS} ≤ -5V, V _{GS} = -10V	-20			A
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = -10V, I _D = -3.6A		106	115	mΩ
		V _{GS} = -4.5V, I _D = -2.6A		115	125	
g _{FS}	Forward Transconductance	V _{DS} = -15V, I _D = -2.6A		12		S
V _{SD}	Diode Forward Voltage	I _S = -2A, V _{GS} =0V		-0.8	-1.2	V
Dynamic						
Q _g	Total Gate Charge	V _{DS} =-30V, V _{GS} =-10V, I _D =-3.0A		12	20	nC
Q _{gs}	Gate-Source Charge			2.5		
Q _{gd}	Gate-Drain Charge			3.5		
C _{iss}	Input Capacitance	V _{DS} =-30V, V _{GS} =0V, f=1MHz		900		pF
C _{oss}	Output Capacitance			90		
C _{rss}	Reverse Transfer Capacitance			40		
t _{d(on)}	Turn-On Time	V _{DD} =-30V, R _L =7.5Ω, I _D =-2.6A, V _{GEN} =-10V, R _G =3Ω		10	20	ns
t _r				6	10	
t _{d(off)}	Turn-Off Time			30	45	
t _f				12	25	

Typical Performance Characteristics

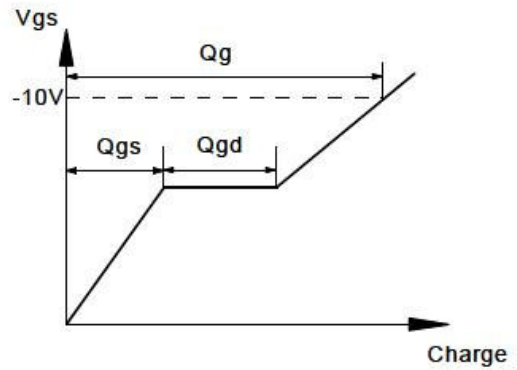
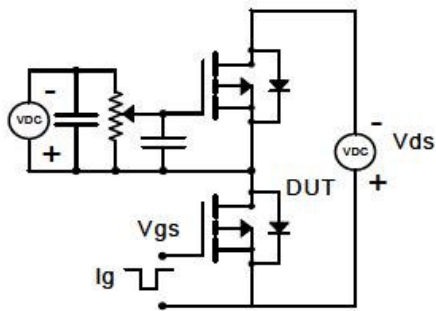


Typical Performance Characteristics (continue)

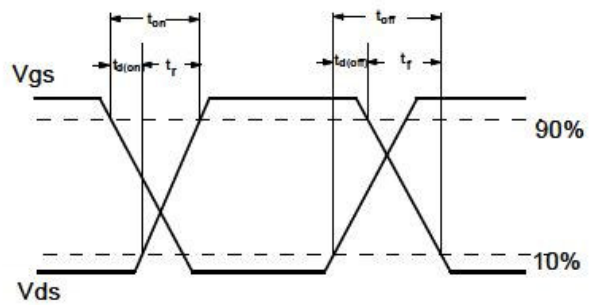
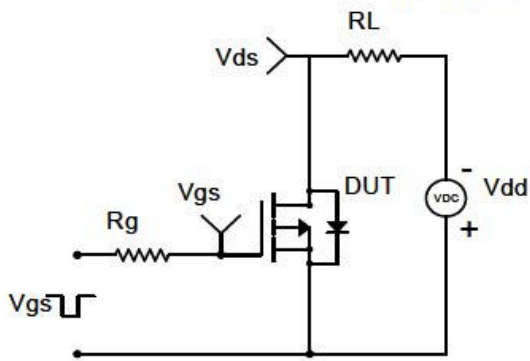


Typical Characteristics

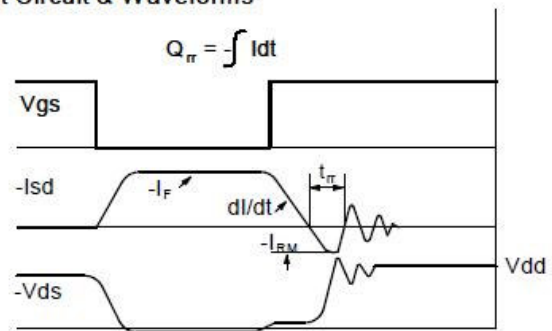
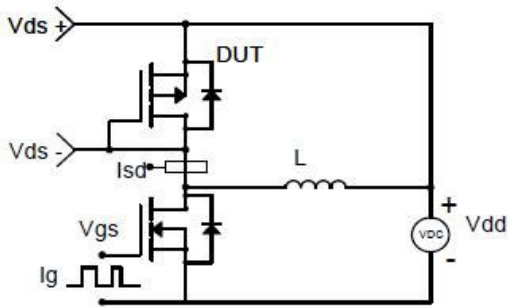
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

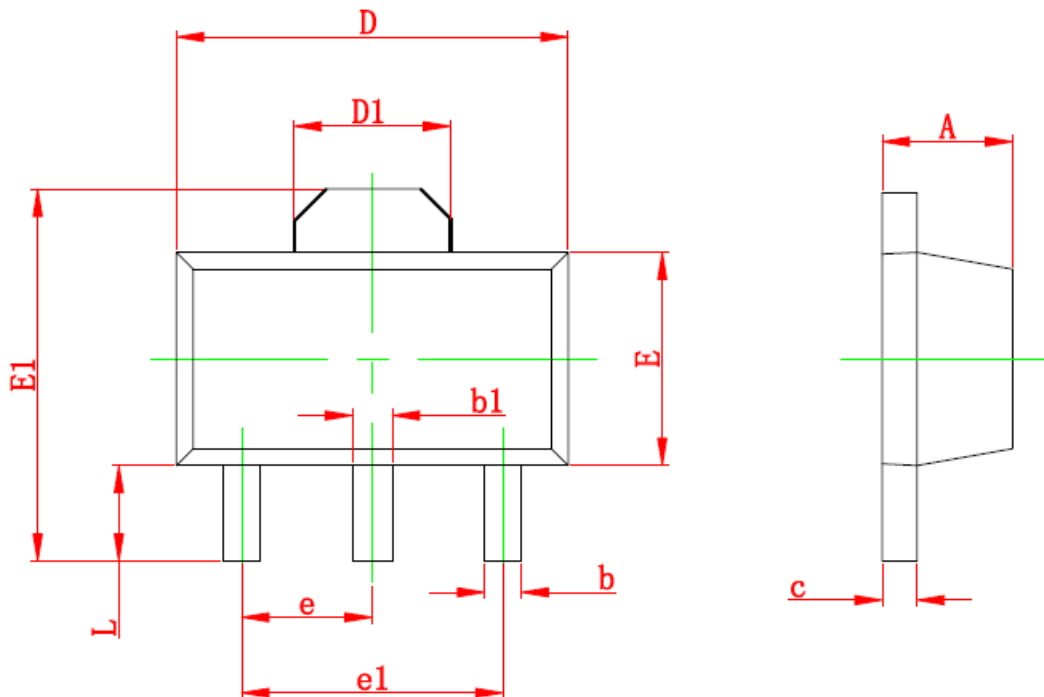


Diode Recovery Test Circuit & Waveforms



Package Dimension

SOT-89-3L







Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.197
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 (REF)		0.061 (REF)	
E	2.30	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.50 (TYP)		0.060 (TYP)	
e1	3.00 (TYP)		0.118 (TYP)	
L	0.900 (TYP)	1.200	0.035	0.047



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